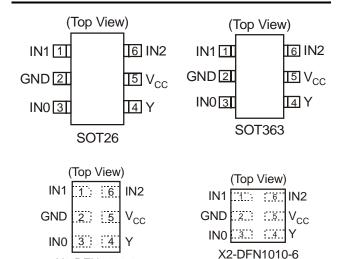


### **Description**

The 74LVC1G58 is a single 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions AND, OR, NAND, NOR, XOR, inverter or non-inverting buffer. All inputs can be connected to ground or V<sub>CC</sub> as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates, but may respond differently due to the Schmitt action at the inputs.

### **Pin Assignments**



#### **Features**

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
  - 200-V Machine Model (A115-A)
  - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- · Range of Package Options
- SOT26, SOT363, DF1410, and DFN1010: Available in "Green" Molding Compound (no Br, Sb)
- · Lead Free Finish/ RoHS Compliant (Note 1)
  - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
  - Halogen and Antimony Free. "Green" Device (Note 3)

### **Applications**

- Voltage Level Shifting
- General Purpose Logic
- · Power Down Signal Isolation

X2-DFN1410-6

- Wide array of products such as:
  - PCs, networking, notebooks, netbooks, PDAs
  - Computer peripherals, hard drives, CD/DVD ROM
  - TV, DVD, DVR, set top box
  - Cell Phones, Personal Navigation / GPS
  - MP3 players ,Cameras, Video Recorders

Notes:

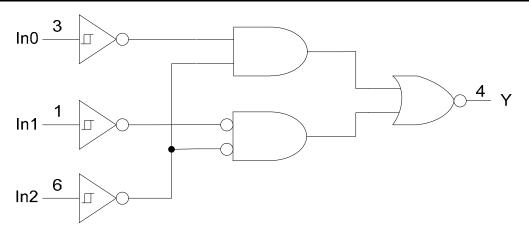
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



# **Pin Descriptions**

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Y	Data Output
V <sub>CC</sub>	Supply Voltage
IN2	Data Input

# **Logic Diagram**

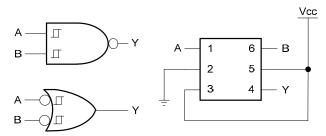


### **Function Table**

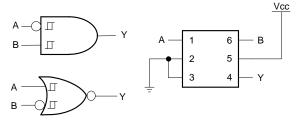
	Inputs	Output	
IN2	IN1	IN0	Υ
L	L	L	L
L	L	Н	Н
L	Н	L	L
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	L



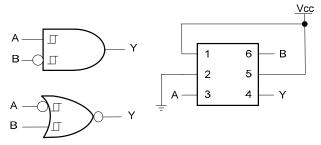
# **Logic Configurations**



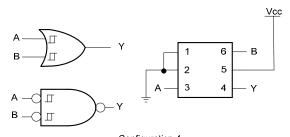
Configuration 1
2-Input NAND Gate
2-Input OR Gate with Both Inputs Inverted



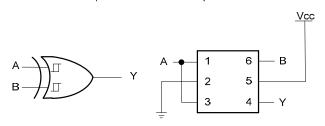
Configuration 2 2-Input AND Gate with A Input Inverted 2-Input NOR Gate with B input Inverted



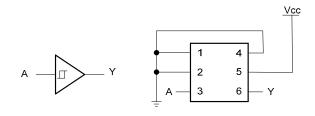
Configuration 3
2-Input AND Gate with B Input Inverted
2-Input NOR Gate with A Input Inverted



Configuration 4
2-Input OR Gate
2-Input NAND Gate with Both Inputs Inverted



Configuration 5 2-Input XOR Gate



Configuration 6 Buffer

Function Selection Table							
Logic Function	Configuration						
2-input NAND	1						
2-input NAND with both inputs inverted	4						
2-input AND with inverted input	2, 3						
2-input NOR with inverted input	2, 3						
2-input OR	4						
2-input OR with both inputs inverted	1						
2-input XOR	5						
1-input Buffer	6						



# **Absolute Maximum Ratings (Note 4)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
Vı	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
lıĸ	Input Clamp Current V <sub>I</sub> < 0	-50	mA
lok	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
$T_J$	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Notes:

### **Recommended Operating Conditions (Note 5)**

Symbol		Parameter	Min	Max	Unit
V	On a ration Walterna	Operating	1.65	5.5	V
V <sub>CC</sub>	Operating Voltage	Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	Vcc	V
		V <sub>CC</sub> = 1.65V		-4	
		V <sub>CC</sub> = 2.3V		-8	
I <sub>OH</sub>	High-level output current			-16	mA
		Vcc = 3V		-24	
		V <sub>CC</sub> = 4.5V		-32	
		V <sub>CC</sub> = 1.65V		4	
		V <sub>CC</sub> = 2.3V		8	
I <sub>OL</sub>	Low-level output current			16	mA
		Vcc = 3V		24	
		V <sub>CC</sub> = 4.5V		32	
		$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20	
Δt/ΔV	Input transition rise or fall rate	V <sub>CC</sub> = 3.3V ± 0.3V		10	ns/V
		V <sub>CC</sub> = 5V ± 0.5V		5	
T <sub>A</sub>	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at  $V_{\text{CC}}$  or Ground.

<sup>4.</sup> Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



# Electrical Characteristics $T_A = -40$ °C to +85°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
$V_{T+}$	Positive-going input threshold voltage		3V	1.50		2.00	
	tilleshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V <sub>T-</sub>	Negative-going input threshold voltage		3V	0.80		1.30	
	tilleshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
	$\Delta V_T$ Hysteresis $(V_{T+} - V_{T-})$		2.3V	0.40		0.80	
$\Delta V_T$			3V	0.35		1.00	
			4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> - 0.1			
		$I_{OH} = -4mA$	1.65V	1.2			
.,		$I_{OH} = -8mA$	2.3V	1.9			.,
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -16mA	21.6	2.4			V
		I <sub>OH</sub> = -24mA	3V	2.3			
		I <sub>OH</sub> = -32mA	4.5V	3.8			
		I <sub>OL</sub> = 100μA	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.45	
.,		I <sub>OL</sub> = 8mA	2.3V			0.3	.,
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 16mA	21.6			0.4	V
		I <sub>OL</sub> = 24mA	3V			0.55	
		I <sub>OL</sub> = 32mA	4.5			0.55	
II	Input Current	V <sub>I</sub> = 5.5V or GND	0 to 5.5V			± 5	μΑ
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μA
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			10	μΑ
ΔI <sub>CC</sub>	Additional Supply Current	One input at $V_{CC}$ -0.6V Other inputs at $V_{CC}$ or GND	3V to 5.5V		,	500	μΑ



# Electrical Characteristics $T_A = -40$ °C to +125°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
$V_{T+}$	Positive-going input		3V	1.50		2.00	
	threshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
			2.3V	0.58		1.03	
$V_{T-}$	Negative-going input		3V	0.80		1.33	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
	$\Delta V_T$ Hysteresis $(V_{T+} - V_{T-})$		2.3V	0.37		0.80	
$\Delta V_{T}$			3V	0.32		1.00	
			4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> -0.1			
		I <sub>OH</sub> = -4mA	1.65V	0.95			
		I <sub>OH</sub> = -8mA	2.3V	1.7			.,
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -16mA	0)/	1.9			V
		I <sub>OH</sub> = -24mA	3V	2.0			
		I <sub>OH</sub> = -32mA	4.5V	3.4			
		$I_{OL} = 100 \mu A$	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.7	
	18.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.	I <sub>OL</sub> = 8mA	2.3V			0.45	.,
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 16mA	0)/			0.6	V
		I <sub>OL</sub> = 24mA	3V			0.8	
		I <sub>OL</sub> = 32mA	4.5			0.8	
II	Input Current	V <sub>I</sub> = 5.5V or GND	0 to 5.5V			± 100	μΑ
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 200	μA
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			200	μΑ
ΔI <sub>CC</sub>	Additional Supply Current	One input at V <sub>CC</sub> -0.6V Other inputs at V <sub>CC</sub> or GND	3V to 5.5V			5000	μΑ



# Electrical Characteristics (All typical values are at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = +25°C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
C <sub>I</sub>	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF
	Thermal Resistance Junction-	SOT26			204		
		SOT363	(Note 6)		371		0=
$\theta_{JA}$	to-Ambient	X2-DFN1410-6			430		°C/W
		X2-DFN1010-6			510		
		SOT26			52		
	Thermal Resistance Junction-	SOT363	(Note 6)		143		°C/W
θ <sub>JC</sub>	to-Case	X2-DFN1410-6			190		
		X2-DFN1010-6			250		

Notes:

### **Switching Characteristics**

 $T_A = -40$ °C to +85°C, CL = 30 or 50pF as noted (see Figure 1)

Parameter	From	TO	V <sub>CC</sub> = 1.8V ± 0.15V				V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V		Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Υ	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

 $T_A = -40$ °C to +125°C, CL = 30 or 50pF as noted (see Figure 1)

Parameter	meter TO		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V		Unit
	(Input)	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Υ	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

# **Operating Characteristics**

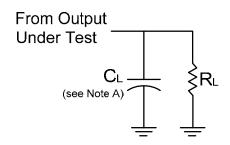
#### $T_A = +25$ °C

	Parameter	Test Conditions	V <sub>CC</sub> = 1.8V Typ.	V <sub>CC</sub> = 2.5V Typ.	V <sub>CC</sub> = 3.3V Typ.	V <sub>CC</sub> = 5V Typ.	Unit
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

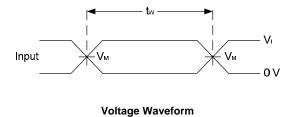
<sup>6.</sup> Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



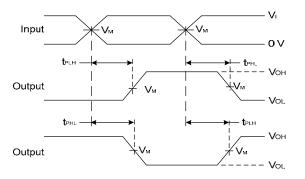
### **Parameter Measurement Information**



Vcc	Inj	outs	V <sub>M</sub>	CL	RL	
100	VI	t <sub>r</sub> /t <sub>f</sub>	T IVI	51	L	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1ΚΩ	
2.5V±0.2V	Vcc	≤2ns	V <sub>CC</sub> /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω	



Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10 MHz

C. Inputs are measured separately one transition per measurement

D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$ 

7: Tape & Reel



Logic Device

### CONFIGURABLE MULTIPLE-FUNCTION GATE

### **Ordering Information**

74LVC1G 58 XXX - 7

Function Package Packing

74 : Logic Prefix 58 : 3-Input W6 : SOT26 LVC : 1.65 to 5.5V Configurable DW : SOT363

Family Multiple-Function FW4: X2-DFN1010-6 1G: One gate Gate FZ4: X2-DFN1410-6

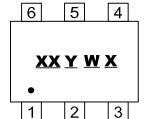
	Budan 0		Packaging	7" Tape and Reel	
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix
<b>Pb</b> ,	74LVC1G58W6-7	W6	SOT26	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVC1G58DW-7	DW	SOT363	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVC1G58FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
<b>Pb</b> ,	74LVC1G58FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



### **Marking Information**

#### (1) SOT26, SOT363



XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G58W6	SOT26	TX
74LVC1G58DW	SOT363	TX

#### (2) X2-DFN1010-6, X2-DFN1410-6

### (Top View)



XX : Identification Code

<u>7</u> : Year : 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

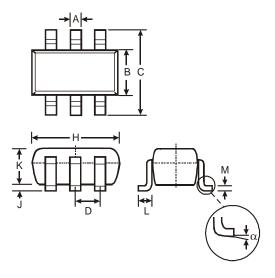
52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G58FW4	X2-DFN1010-6	TX
74LVC1G58FZ4	X2-DFN1410-6	TX



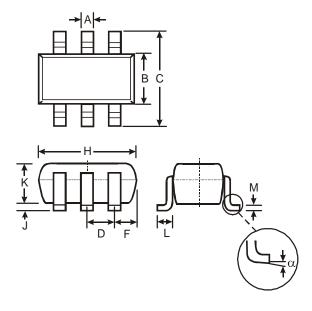
# Package Outline Dimensions (All Dimensions in mm)

### (1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
С	2.70	3.00	2.80	
D	_	_	0.95	
Н	2.90	3.10	3.00	
J	0.013	0.10	0.05	
K	1.00	1.30	1.10	
L	0.35	0.55	0.40	
M	0.10	0.20	0.15	
α	0°	8°		
All Dimensions in mm				

#### (2) SOT363

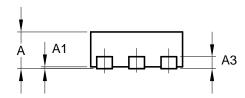


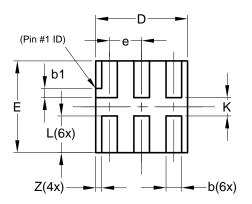
SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
K	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



# Package Outline Dimensions (All Dimensions in mm)

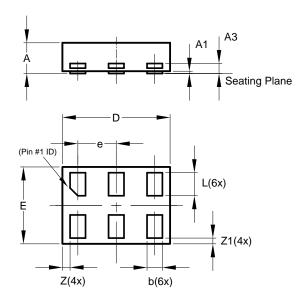
#### (3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
А3	_		0.13	
p	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_		0.35	
Г	0.35	0.45	0.40	
K	0.15			
Z	_		0.065	
All Dimensions in mm				

### (4) X2-DFN1410-6

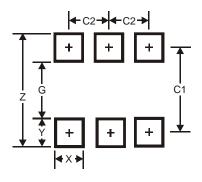


X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
А3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
E	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
<b>Z</b> 1	0.045	0.105	0.075	
All Dimensions in mm				



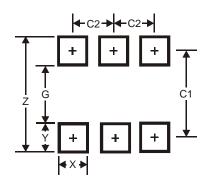
# **Suggest Pad Layout**

### (1) SOT26



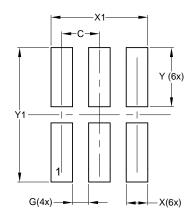
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

### (2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

#### (3) X2-DFN1010-6

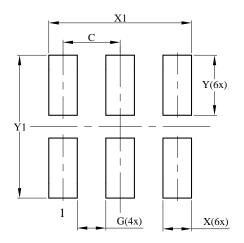


Dimensions	Value	
פווטופוופווטווט	(in mm)	
С	0.350	
G	0.150	
Х	0.200	
X1	0.900	
Y	0.550	
Y1	1.250	



# **Suggest Pad Layout**

### (4) X2-DFN1410-6



Dimensions	Value	
Dilliensions	(in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	



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